

SDT1216-VB Datasheet

P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) | Q_g (Typ.) |
|--------------|----------------------------|-----------|--------------|
| - 20 | 0.030 at $V_{GS} = -4.5$ V | -10^a | 18 nC |
| | 0.040 at $V_{GS} = -2.5$ V | $-g^a$ | |

FEATURES

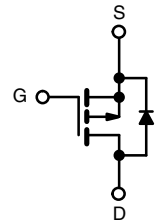
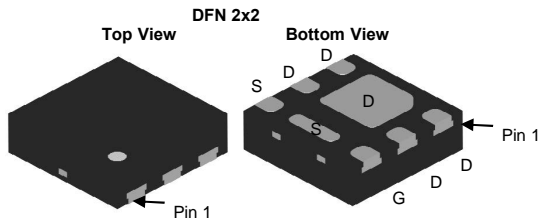
- Trench Power MOSFET
- Thermally Enhanced DFN2X2 Package
- Small Footprint Area
- Low On-Resistance



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch, PA Switch, and Battery Switch for Portable Devices



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|--------------|------------------|
| Drain-Source Voltage | V_{DS} | - 20 | V |
| Gate-Source Voltage | V_{GS} | ± 12 | |
| Continuous Drain Current ($T_J = 150^\circ\text{C}$) | I_D | -10^a | A |
| | | -8^a | |
| | | $-10^{b,c}$ | |
| | | $-8^{b,c}$ | |
| Pulsed Drain Current ($t = 300 \mu\text{s}$) | I_{DM} | - 30 | |
| Continuous Source-Drain Diode Current | I_S | -10^a | |
| | | $-2.5^{b,c}$ | |
| Maximum Power Dissipation | P_D | 17 | W |
| | | 11 | |
| | | $3.3^{b,c}$ | |
| | | $2.1^{b,c}$ | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | $^\circ\text{C}$ |
| Soldering Recommendations (Peak Temperature) ^{d, e} | | 250 | |

THERMAL RESISTANCE RATINGS

| Parameter | | Symbol | Typical | Maximum | Unit |
|---|--------------|------------|---------|---------|--------------------|
| Maximum Junction-to-Ambient ^{b, f} | $t \leq 5$ s | R_{thJA} | 28 | 38 | $^\circ\text{C/W}$ |
| Maximum Junction-to-Case (Drain) | Steady State | R_{thJC} | 5.6 | 7.5 | |

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. $t = 5$ s.

d. See solder profile The DFN2X2 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

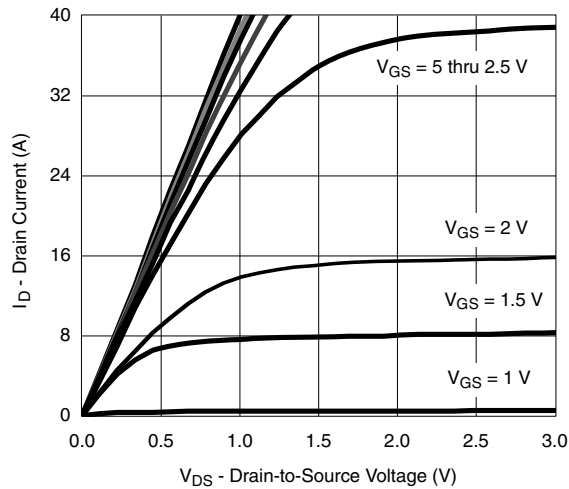
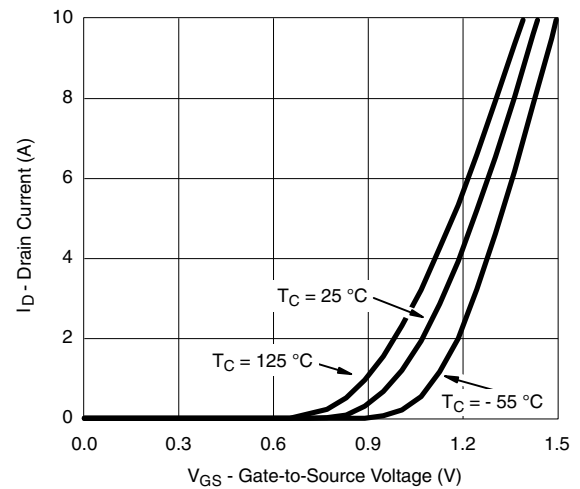
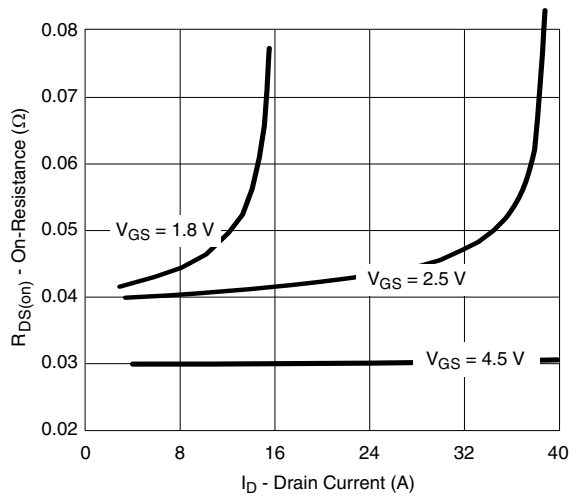
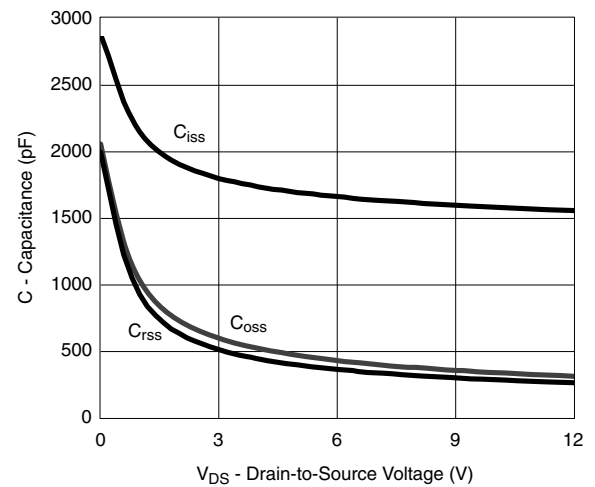
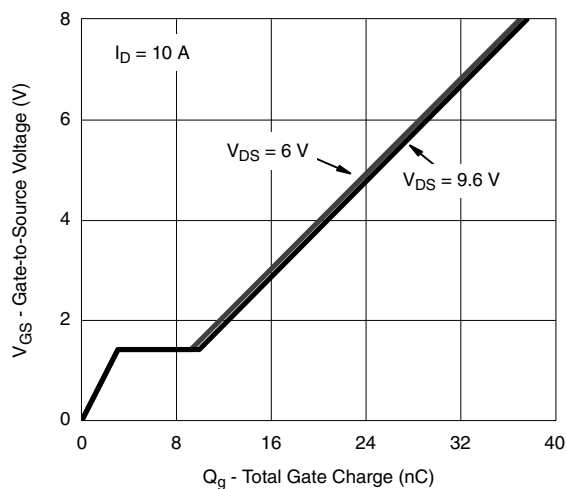
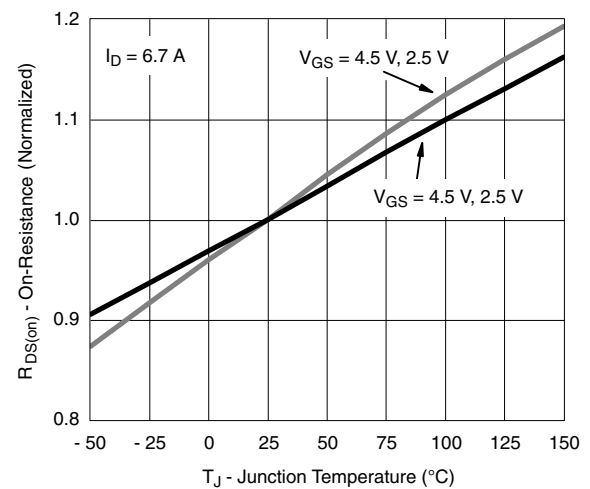
f. Maximum under steady state conditions is 80°C/W .

| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | |
|---|--------------------------------------|--|-------|-------|-------|-------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = - 250 μA | - 20 | | | V |
| V _{DS} Temperature Coefficient | ΔV _{DS} /T _J | I _D = - 250 μA | | - 11 | | mV/°C |
| V _{GS(th)} Temperature Coefficient | ΔV _{GS(th)} /T _J | | | 2.7 | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = - 250 μA | - 0.4 | | - 1 | V |
| Gate-Source Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 8 V | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = - 12 V, V _{GS} = 0 V | | | - 1 | μA |
| | | V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 55 °C | | | - 10 | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V | - 20 | | | A |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = - 4.5 V, I _D = - 6.7 A | | 0.030 | | Ω |
| | | V _{GS} = - 2.5 V, I _D = - 6.2 A | | 0.040 | | |
| | | V _{GS} = - 1.8 V, I _D = - 2.3 A | | 0.042 | | |
| | | V _{GS} = - 1.5 V, I _D = - 1 A | | 0.050 | | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = - 10 V, I _D = - 6.7 A | | 30 | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz | | 1600 | | pF |
| Output Capacitance | C _{oss} | | | 430 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 370 | | |
| Total Gate Charge | Q _g | V _{DS} = - 6 V, V _{GS} = - 8 V, I _D = - 10 A | | 38 | 54 | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} = - 6 V, V _{GS} = - 4.5 V, I _D = - 10 A | | 23 | 33 | |
| Gate-Drain Charge | Q _{gd} | | | 3 | | |
| Gate Resistance | R _g | | | 6.5 | | |
| Gate Resistance | R _g | f = 1 MHz | | 7 | | Ω |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = - 6 V, R _L = 0.75 Ω I _D ≅ - 8 A, V _{GEN} = - 4.5 V, R _g = 1 Ω | | 20 | 30 | ns |
| Rise Time | t _r | | | 40 | 60 | |
| Turn-Off Delay Time | t _{d(off)} | | | 65 | 100 | |
| Fall Time | t _f | | | 40 | 60 | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = - 6 V, R _L = 0.75 Ω I _D ≅ - 8 A, V _{GEN} = - 8 V, R _g = 1 Ω | | 10 | 15 | |
| Rise Time | t _r | | | 12 | 20 | |
| Turn-Off Delay Time | t _{d(off)} | | | 70 | 105 | |
| Fall Time | t _f | | | 40 | 60 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | - 10 | A |
| Pulse Diode Forward Current | I _{SM} | | | | 30 | |
| Body Diode Voltage | V _{SD} | I _S = - 8 A, V _{GS} = 0 V | | - 0.8 | - 1.2 | V |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = - 8 A, di/dt = 100 A/μs, T _J = 25 °C | | 40 | 60 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | 20 | 30 | nC |
| Reverse Recovery Fall Time | t _a | | | 14 | | ns |
| Reverse Recovery Rise Time | t _b | | | 26 | | |

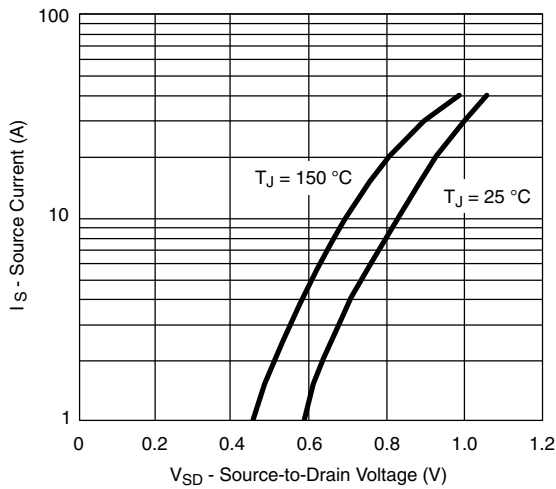
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

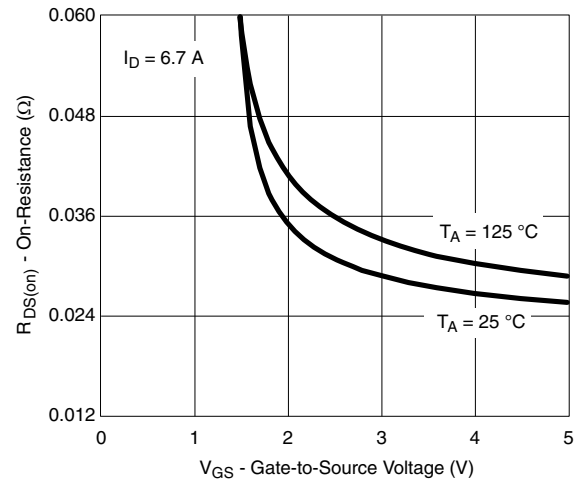
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

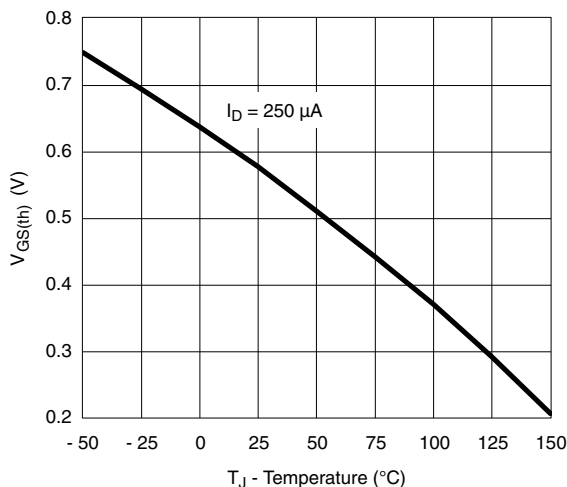
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



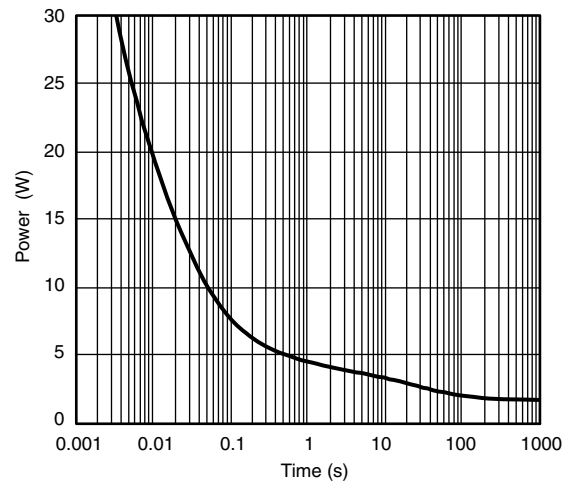
Source-Drain Diode Forward Voltage



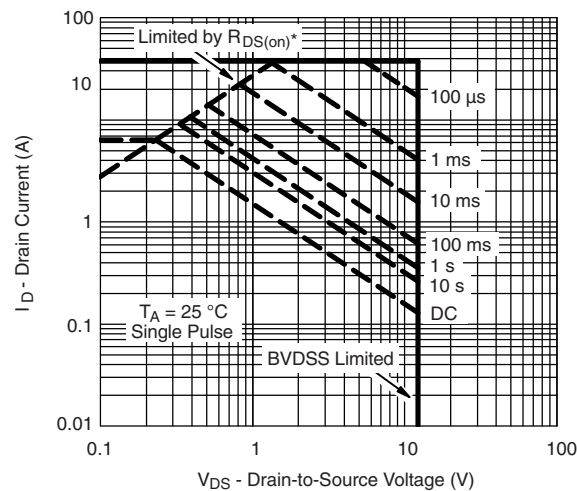
On-Resistance vs. Gate-to-Source Voltage



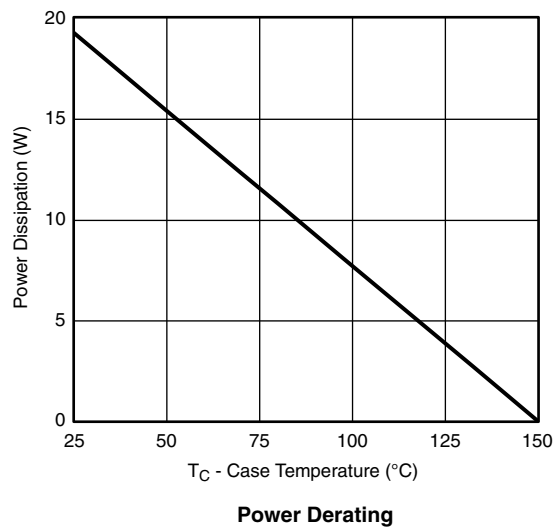
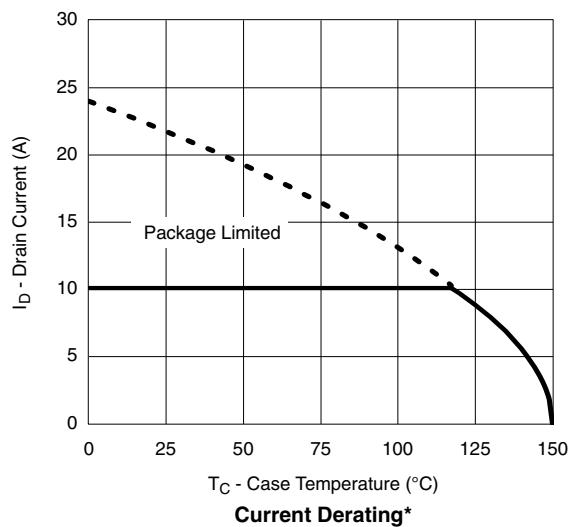
Threshold Voltage



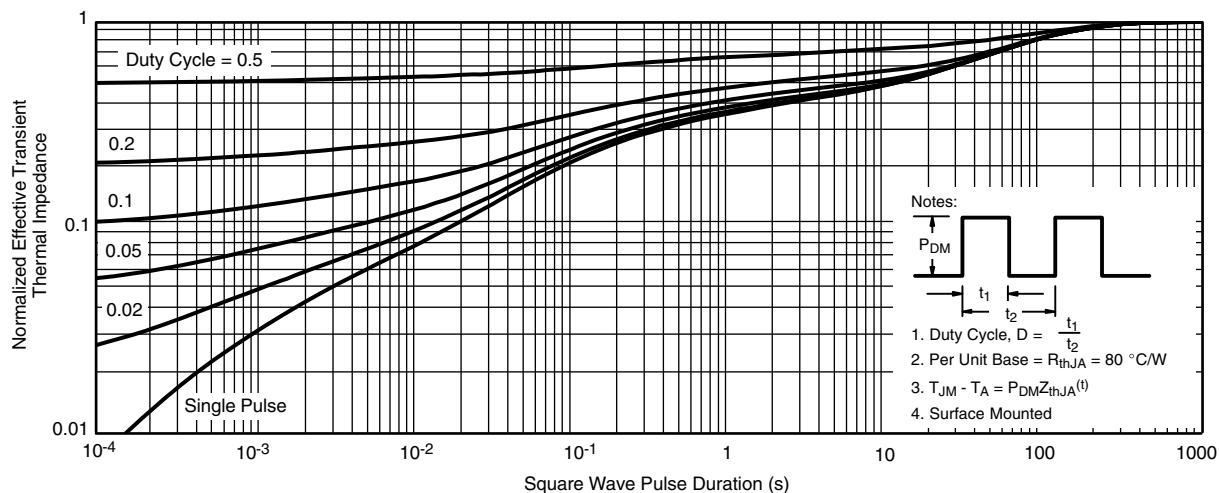
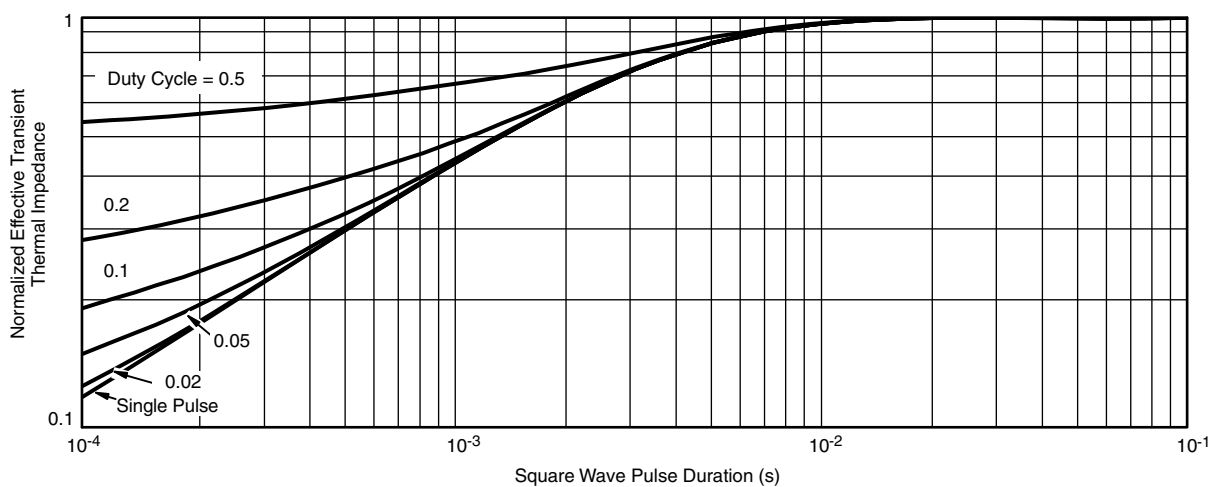
Single Pulse Power, Junction-to-Ambient



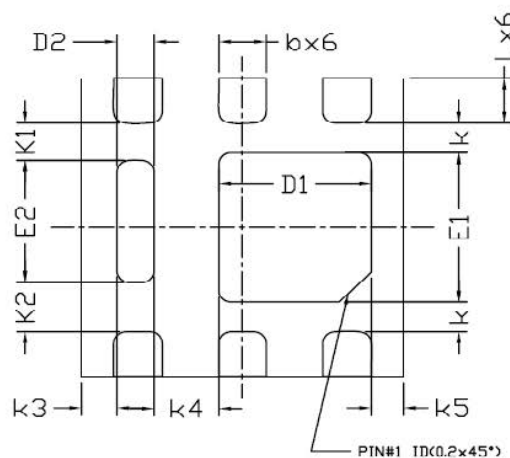
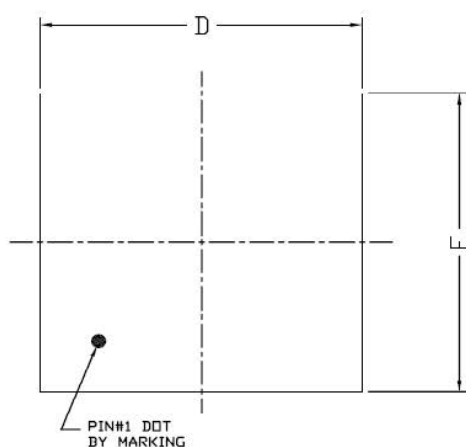
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

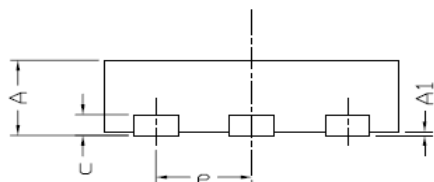
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

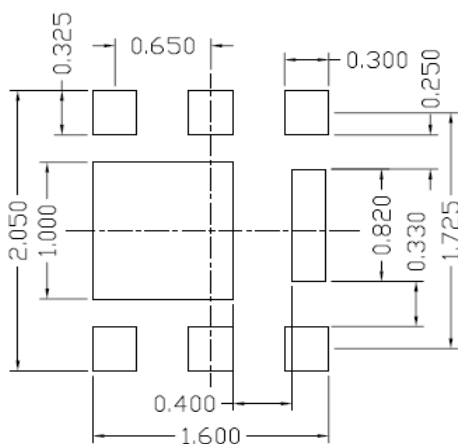
DFN2x2 _6L_EP1_S PACKAGE OUTLINE



BOTTOM VIEW



RECOMMENDED LAND PATTERN



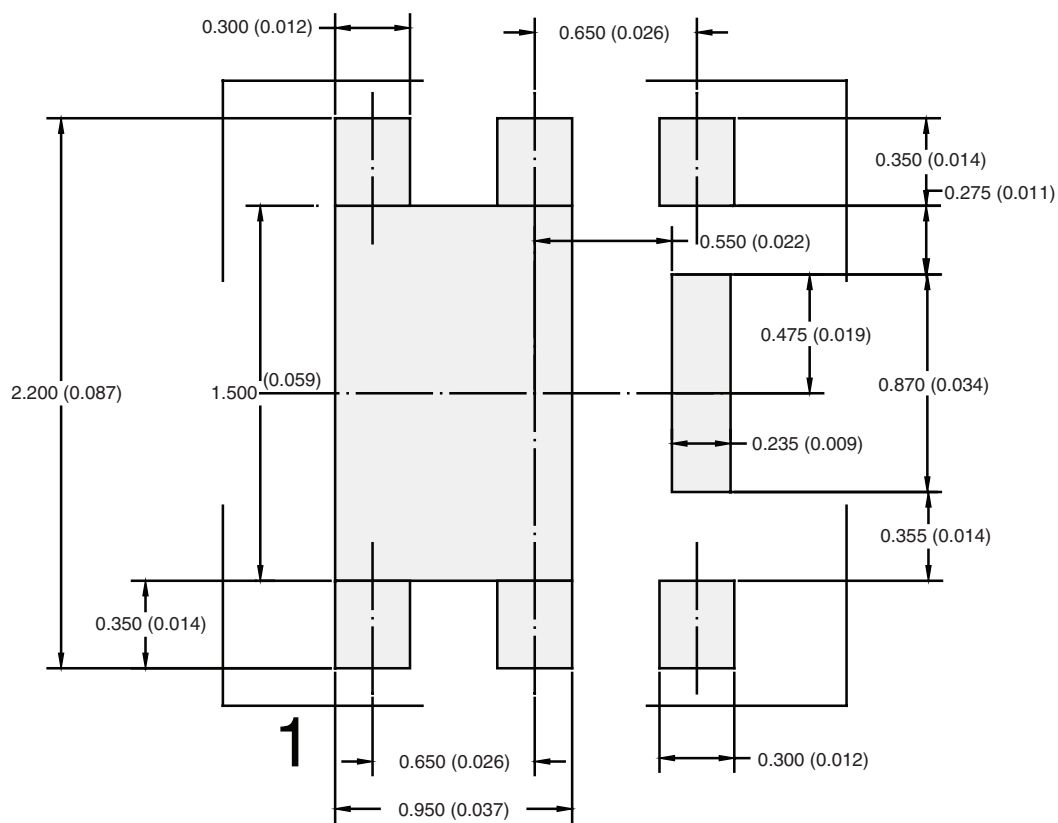
UNIT: mm

NOTE

1. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

| SYMBOLS | DIMENSIONS IN MILLIMETERS | | | DIMENSIONS IN INCHES | | |
|---------|---------------------------|------|------|----------------------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.50 | 0.55 | 0.60 | 0.020 | 0.022 | 0.024 |
| A1 | 0.00 | — | 0.05 | 0.000 | — | 0.002 |
| b | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 |
| c | 0.152 REF | | | 0.006 REF | | |
| D | 1.90 | 2.00 | 2.10 | 0.075 | 0.079 | 0.083 |
| D1 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 |
| D2 | 0.13 | 0.23 | 0.33 | 0.005 | 0.009 | 0.013 |
| E | 1.90 | 2.00 | 2.10 | 0.075 | 0.079 | 0.083 |
| E1 | 0.90 | 1.00 | 1.10 | 0.035 | 0.039 | 0.043 |
| E2 | 0.72 | 0.82 | 0.92 | 0.028 | 0.032 | 0.036 |
| e | 0.65 BSC | | | 0.026 BSC | | |
| K | 0.20 BSC | | | 0.008 BSC | | |
| K1 | 0.25 BSC | | | 0.010 BSC | | |
| K2 | 0.33 BSC | | | 0.013 BSC | | |
| K3 | 0.22 BSC | | | 0.009 BSC | | |
| K4 | 0.40 BSC | | | 0.016 BSC | | |
| K5 | 0.20 BSC | | | 0.008 BSC | | |
| L | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 |

RECOMMENDED PAD LAYOUT FOR DFN2X2



Dimensions in mm/(Inches)

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